TENTATIVE

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

2 S A 1 8 0 2

STROBE FLASH APPLICATIONS. MEDIUM POWER AMPLIFIER APPLICATIONS.

- Excellent hFE Linearity
 - : $h_{FE(1)} = 200 \sim 600 \text{ (V}_{CE} = -2\text{V}, I_{C} = -0.5\text{A})$: $h_{FE(2)} = 140 \text{ (Min.) (V}_{CE} = -2\text{V}, I_{C} = -3\text{A})$
- Low Collector Saturation Voltage
 - : $V_{CE(sat)} = -0.5V (Max.) (I_C = -3A, I_B = -60mA)$
- Surface Mount Package: Lead Bending Type 2-7B2A
- Complementary to 2SC4681

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT	
Collector-Base Voltage			v_{CBO}	-30	V	
Collector-Emitter Voltage			v_{CES}	-30	V	
			v_{CEO}	-10		
Emitter-Base Voltage			$V_{ m EBO}$	-6	V	
Collector Current	DC		$I_{\mathbf{C}}$	-3	A	
	Pulsed (Note 1)		I_{CP}	-6		
Base Current			IB	-0.5	A	
Collector Power Dissipation		Ta = 25°C	D -:	1.0	W	
		$Tc = 25^{\circ}C$	$P_{\mathbf{C}}$	10		
Junction Temperature			T_j	150	°C	
Storage Temperature Range			$\mathrm{T_{stg}}$	-55~150	$^{\circ}\mathrm{C}$	

Unit in mm 2.0 MAX 6.8 MAX 0.6 MAX. 0.6 MAX BASE COLLECTOR (FIN) **EMITTER JEDEC EIAJ**

2-7B1A

Weight: 0.36g

TOSHIBA

Note 1: Pulse Test: Pulse Width=10ms (Max.) Duty Cycle = 30% (Max.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_{E} = 0$	_	_	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6V, I_C = 0$	_	_	-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = -10 \text{mA}, I_B = 0$	-10	_	_	v
DC Current Gain	hFE(1)	$V_{CE} = -2V, I_{C} = -0.5A$	200	_	600	
	$h_{ ext{FE}(2)}$	$V_{CE} = -2V$, $I_{C} = -3A$	140	200	_	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_C = -3A, I_B = -60mA$	_	-0.25	-0.50	V
Base-Emitter Voltage	$V_{ m BE}$	$V_{CE} = -2V$, $I_{C} = -3A$	_	-0.86	-1.2	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -2V, I_{C} = -0.5A$	_	180	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$	_	50		рF

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